Amplifier Transistors

PNP Silicon

Features

• These are Pb–Free Devices*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	-50	Vdc
Collector-Base Voltage	V _{CBO}	-60	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous	۱ _C	-100	mAdc
Total Device Dissipation @ $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	P _D	350 2.8	mW mW/°C
Total Device Dissipation @ $T_C = 25^{\circ}C$ Derate above $25^{\circ}C$	P _D	1.0 8.0	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

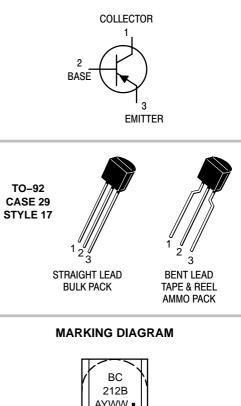
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	357	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	125	°C/W

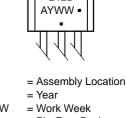
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



ON Semiconductor®

http://onsemi.com





А

Υ

WW = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
BC212BG	TO-92 (Pb-Free)	5000 Units / Bulk
BC212BRL1G	TO–92 (Pb–Free)	2000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

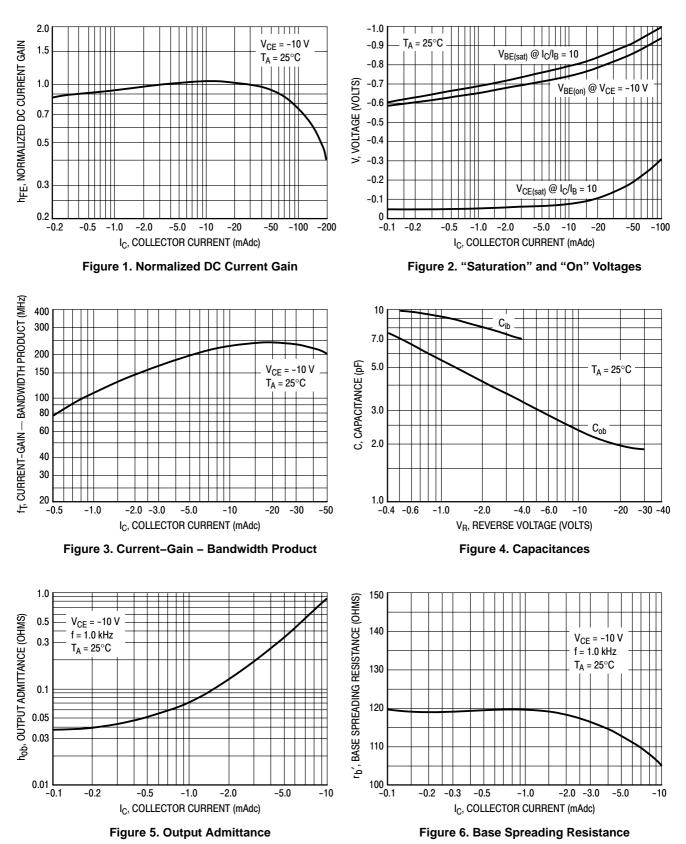
© Semiconductor Components Industries, LLC, 2007 March, 2007 - Rev. 4

BC212B

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
Collector – Emitter Breakdown Voltage	V _{(BR)CEO}	-50	-	-	Vdc
Collector – Base Breakdown Voltage	V _{(BR)CBO}	-60	-	-	Vdc
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5	-	-	Vdc
Collector-Emitter Leakage Current	I _{CBO}	-	-	-15	nAdc
Emitter-Base Leakage Current	I _{EBO}	-	-	-15	nAdc
ON CHARACTERISTICS					
DC Current Gain (I _C = −10 μAdc, V _{CE} = −5.0 Vdc)	h _{FE}	40	-	-	-
$(I_C = -2.0 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc})$		60	-	-	
(I _C = -100 mAdc, V _{CE} = -5.0 Vdc) (Note 1)		-	120	_	
Collector – Emitter Saturation Voltage ($I_C = -10 \text{ mAdc}, I_B = -0.5 \text{ mAdc}$) ($I_C = -100 \text{ mAdc}, I_B = -5.0 \text{ mAdc}$) (Note 1)	V _{CE(sat)}		-0.10 -0.25	_ _0.6	Vdc
Base – Emitter Saturation Voltage ($I_C = -100$ mAdc, $I_B = -5.0$ mAdc)	V _{BE(sat)}	-	-1.0	-1.4	Vdc
Base–Emitter On Voltage ($I_C = -2.0 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc}$)	V _{BE(on)}	-0.6	-0.62	-0.72	Vdc
DYNAMIC CHARACTERISTICS					
Current-Gain – Bandwidth Product ($I_C = -10 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc}, f = 100 \text{ mHz}$)	f _T	-	280	_	MHz
Common-Base Output Capacitance ($V_{CB} = -10 \text{ Vdc}, I_C = 0, f = 1.0 \text{ mHz}$)	C _{ob}	_	-	6.0	pF
Noise Figure (I _C = -0.2 mAdc, V _{CE} = -5.0 Vdc, R _S = 2.0 kΩ, f = 1.0 kHz, f = 200 Hz)	NF	-	-	10	dB
Small–Signal Current Gain (I _C = –2.0 mAdc, V _{CE} = –5.0 Vdc, f = 1.0 kHz)	h _{fe}	200	-	400	-

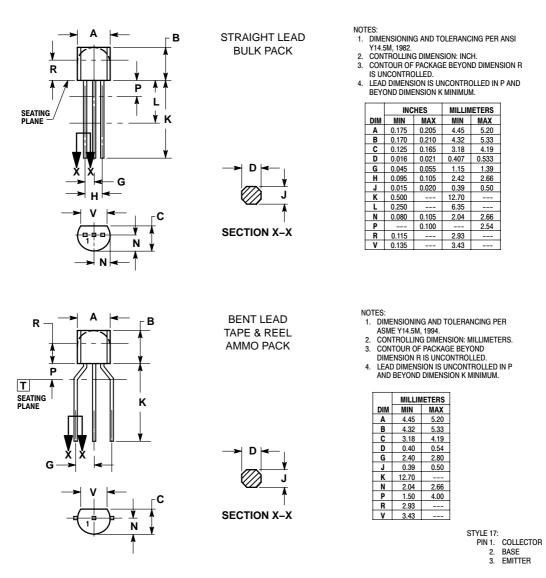
1. Pulse Test: Tp 300 s, Duty Cycle 2.0%.



BC212B

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AM



ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use payes that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunit//Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81–3–5773–3850 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative